

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet 1 of 2

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Complete if Known

<b>Application Number</b>	10/612793
<b>Filing Date</b>	July 2, 2003
<b>First Named Inventor</b>	Bhattacharyya, Arup
<b>Group Art Unit</b>	2811
<b>Examiner Name</b>	Unknown

Attorney Docket No: 1303.111US1

**US PATENT DOCUMENTS**

Examiner Initial*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
PG	US-2003/0042534	03/06/2003	Bhattacharyya, Arup, et al.	257	317	08/30/2001
	US-2003/0072126	04/17/2003	Bhattacharyya, Arup	361	311	08/30/2001
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**EXAMINER**

**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) ? Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		<b>Application Number</b>	10/612793
		<b>Filing Date</b>	July 2, 2003
		<b>First Named Inventor</b>	Bhattacharyya, Arup
		<b>Group Art Unit</b>	2811
		<b>Examiner Name</b>	Unknown
Sheet 2 of 2		Attorney Docket No: 1303.111US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No'	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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*John Farn Gordon*

DATE CONSIDERED

*05/30/04*

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		Filing Date	July 2, 2003
		First Named Inventor	Bhattacharyya, Arup
		Group Art Unit	2826
		Examiner Name	Erdem, Fazli
Sheet 1 of 1		Attorney Docket No: 1303.111US1	

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U.S. DEPARTMENT OF COMMERCE*

**US PATENT DOCUMENTS**

Examiner Initials	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
RE			FAZAN, P , et al., "Capacitor-Less 1-Transistor DRAM", <u>IEEE International SOI Conference</u> , (2002),10-13			

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
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*JMR**PATM 5/2004**May 31, 04*


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